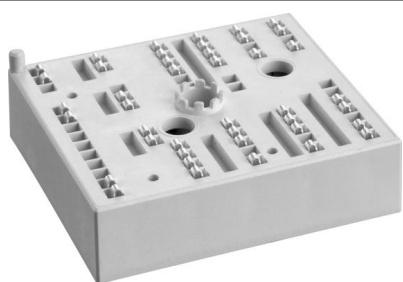


SKiiP 26NAB065V1



MiniSKiiP[®] 2

3-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter
SKiiP 26NAB065V1

Features

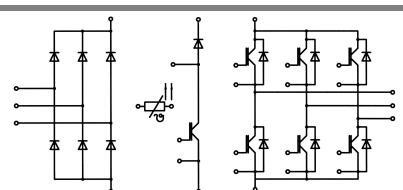
- Ultrafast NPT IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Inverter up to 12,5 kVA
- Typical motor power 5,5 kW

Remarks

- V_{CEsat} , V_F = chip level value



NAB

Absolute Maximum Ratings		$T_c = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter, Chopper			
V_{CES}		600	V
I_C	$T_s = 25\text{ (70) °C}$	56 (42)	A
I_{CRM}	$t_p \leq 1\text{ ms}$	100	A
V_{GES}		± 20	V
T_j		- 40 ... + 150	°C
Diode - Inverter, Chopper			
I_F	$T_s = 25\text{ (70) °C}$	40 (30)	A
I_{FRM}	$t_p \leq 1\text{ ms}$	100	A
T_j		- 40 ... + 150	°C
Diode - Rectifier			
V_{RRM}		800	V
I_F	$T_s = 70\text{ °C}$	61	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180\text{ °, } T_j = 25\text{ °C}$	700	A
i^2t	$t_p = 10\text{ ms, sin } 180\text{ °, } T_j = 25\text{ °C}$	2400	A ² s
T_j		- 40 ... + 150	°C
I_{tRMS}	per power terminal (20 A / spring)	60	A
T_{stg}	$T_{op} \leq T_{stg}$	- 40 ... + 125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_c = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
V_{CEsat}	$I_{Cnom} = 50\text{ A, } T_j = 25\text{ (125) °C}$		2 (2,2)	2,5 (2,7)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1\text{ mA}$	3	4	5	V
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$		1,2 (1,1)	1,3 (1,2)	V
r_T	$T_j = 25\text{ (125) °C}$		16 (22)	24 (30)	mΩ
C_{ies}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		2,7		nF
C_{oes}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		0,8		nF
C_{res}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		0,6		nF
$R_{th(j-s)}$	per IGBT		0,75		K/W
$t_{d(on)}$	under following conditions		35		ns
t_r	$V_{CC} = 300\text{ V, } V_{GE} = \pm 15\text{ V}$		35		ns
$t_{d(off)}$	$I_{Cnom} = 50\text{ A, } T_j = 125\text{ °C}$		240		ns
t_f	$R_{Gon} = R_{Goff} = 15\text{ Ω}$		25		ns
E_{on}	inductive load		1,3		mJ
E_{off}			0,9		mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	$I_{Fnom} = 50\text{ A, } T_j = 25\text{ (125) °C}$		1,9 (1,9)	2,3 (2,4)	V
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,9)	1,1 (1)	V
r_T	$T_j = 25\text{ (125) °C}$		18 (20)	24 (28)	mΩ
$R_{th(j-s)}$	per diode		1,5		K/W
I_{RRM}	under following conditions		42		A
Q_{rr}	$I_{Fnom} = 50\text{ A, } V_R = 300\text{ V}$		3,6		μC
E_{rr}	$V_{GE} = 0\text{ V, } T_j = 125\text{ °C}$		0,8		mJ
	$di_F/dt = 1500\text{ A/μs}$				
Diode - Rectifier					
V_F	$I_{Fnom} = 35\text{ A, } T_j = 25\text{ °C}$		1,1		V
$V_{(TO)}$	$T_j = 150\text{ °C}$		0,8		V
r_T	$T_j = 150\text{ °C}$		11		mΩ
$R_{th(j-s)}$	per diode		0,9		K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) °C}$		1000(1670)		Ω
Mechanical Data					
w			65		g
M_s	Mounting torque	2		2,5	Nm

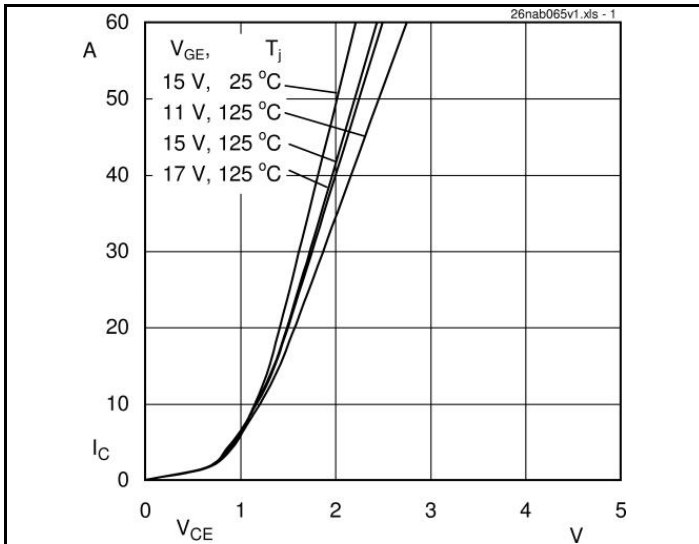


Fig. 1 Typ. output characteristic

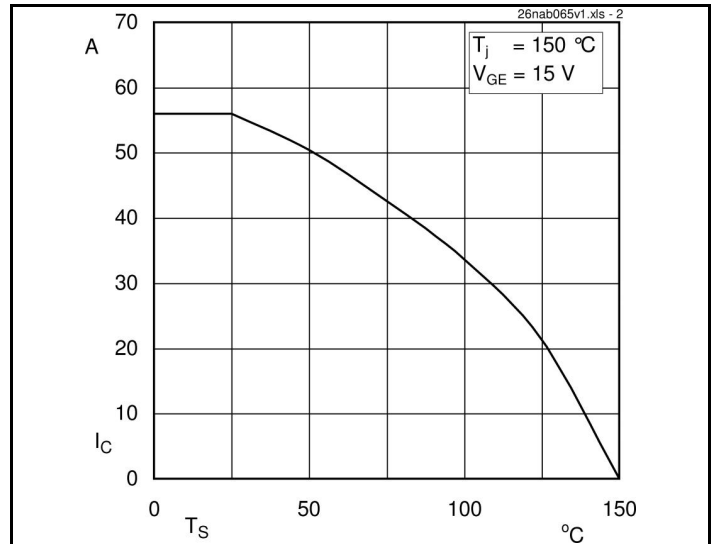


Fig. 2 Typ. rated current vs. temperature

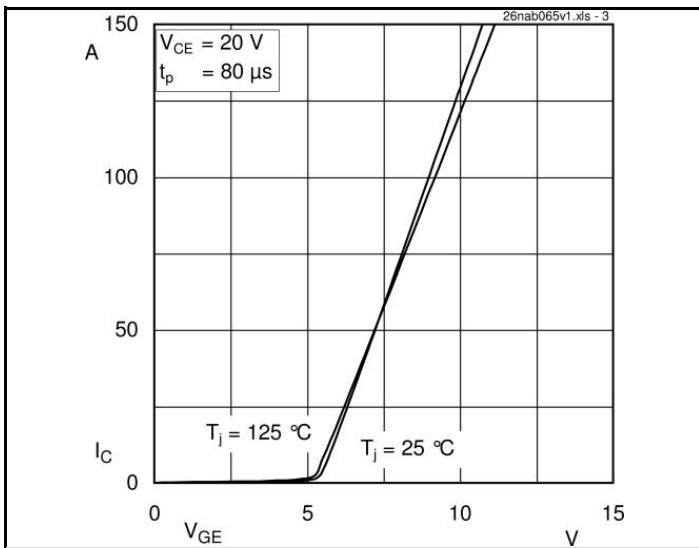


Fig. 3 Typ. transfer characteristic

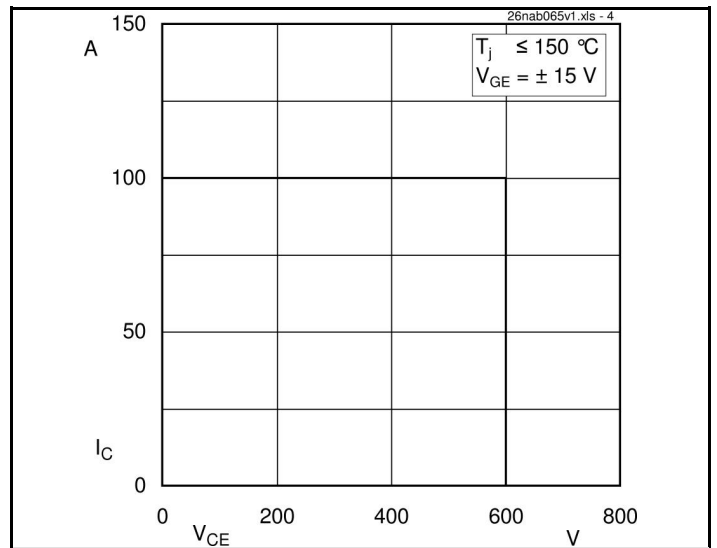


Fig. 4 Reverse bias safe operating area

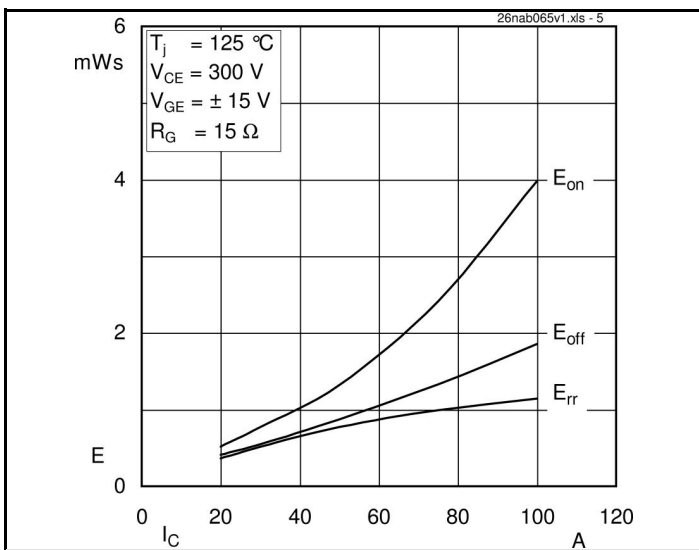


Fig. 5 Typ. Turn-on /-off energy = $f(I_C)$

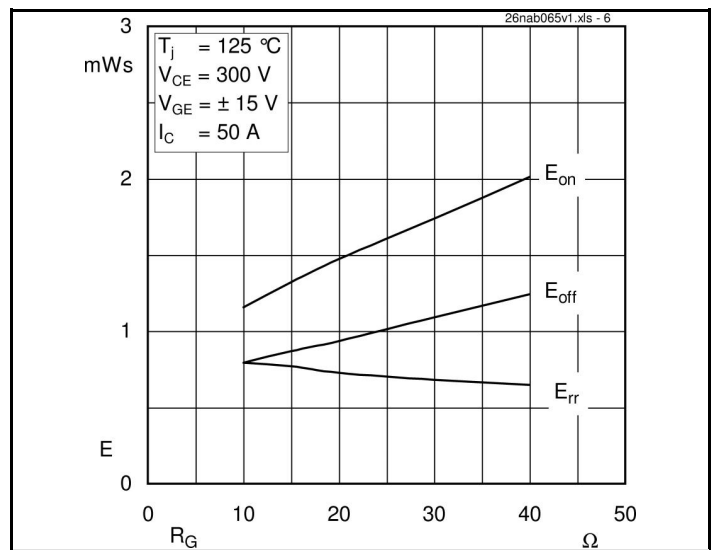


Fig. 6 Typ. Turn-on /-off energy = $f(R_G)$

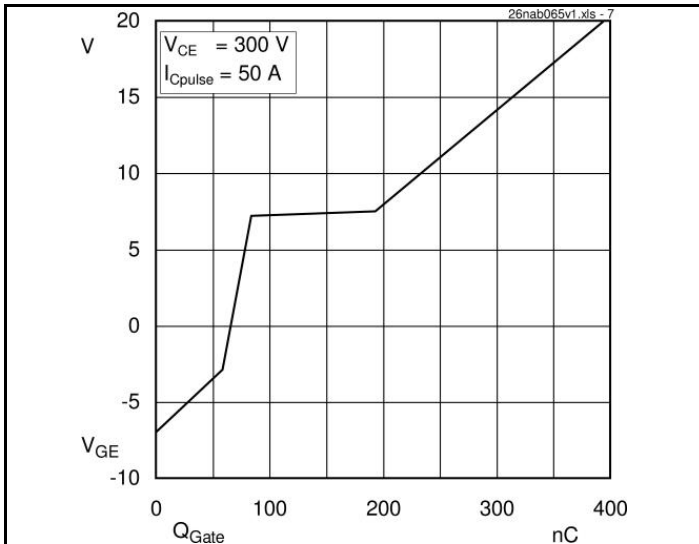


Fig. 7 Typ. gate charge characteristic

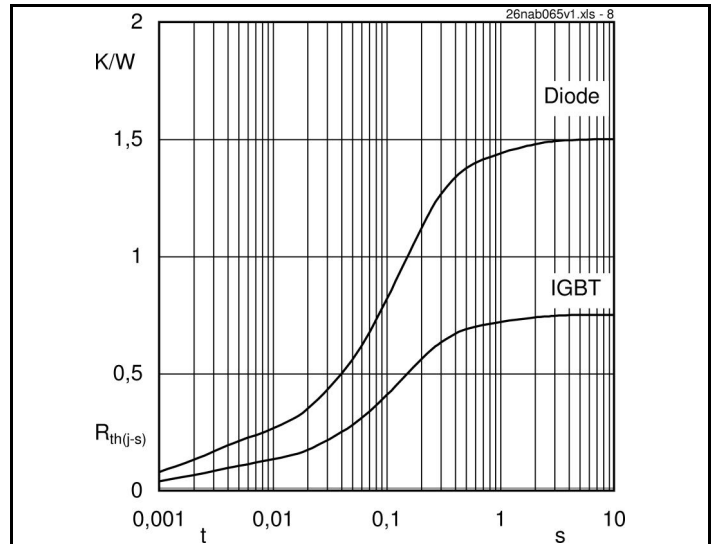


Fig. 8 Typ. thermal impedance

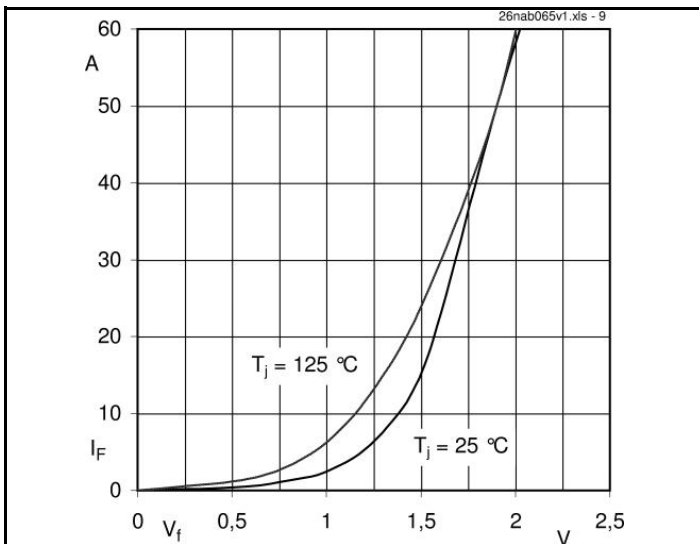


Fig. 9 Typ. freewheeling diode forward characteristic

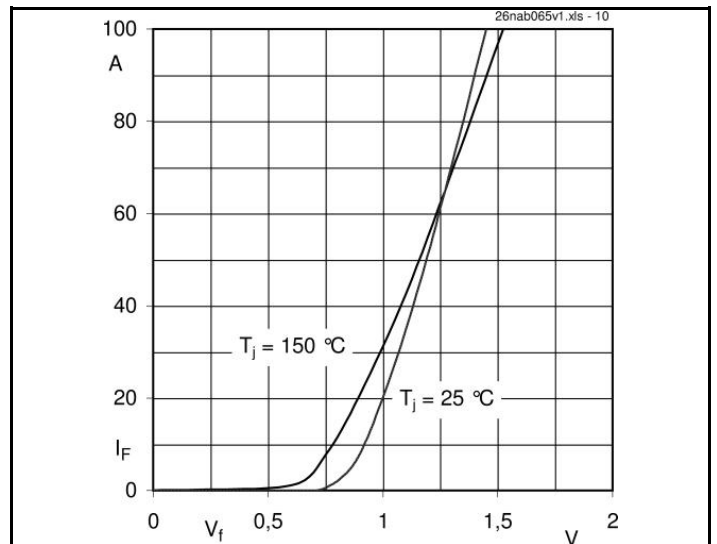
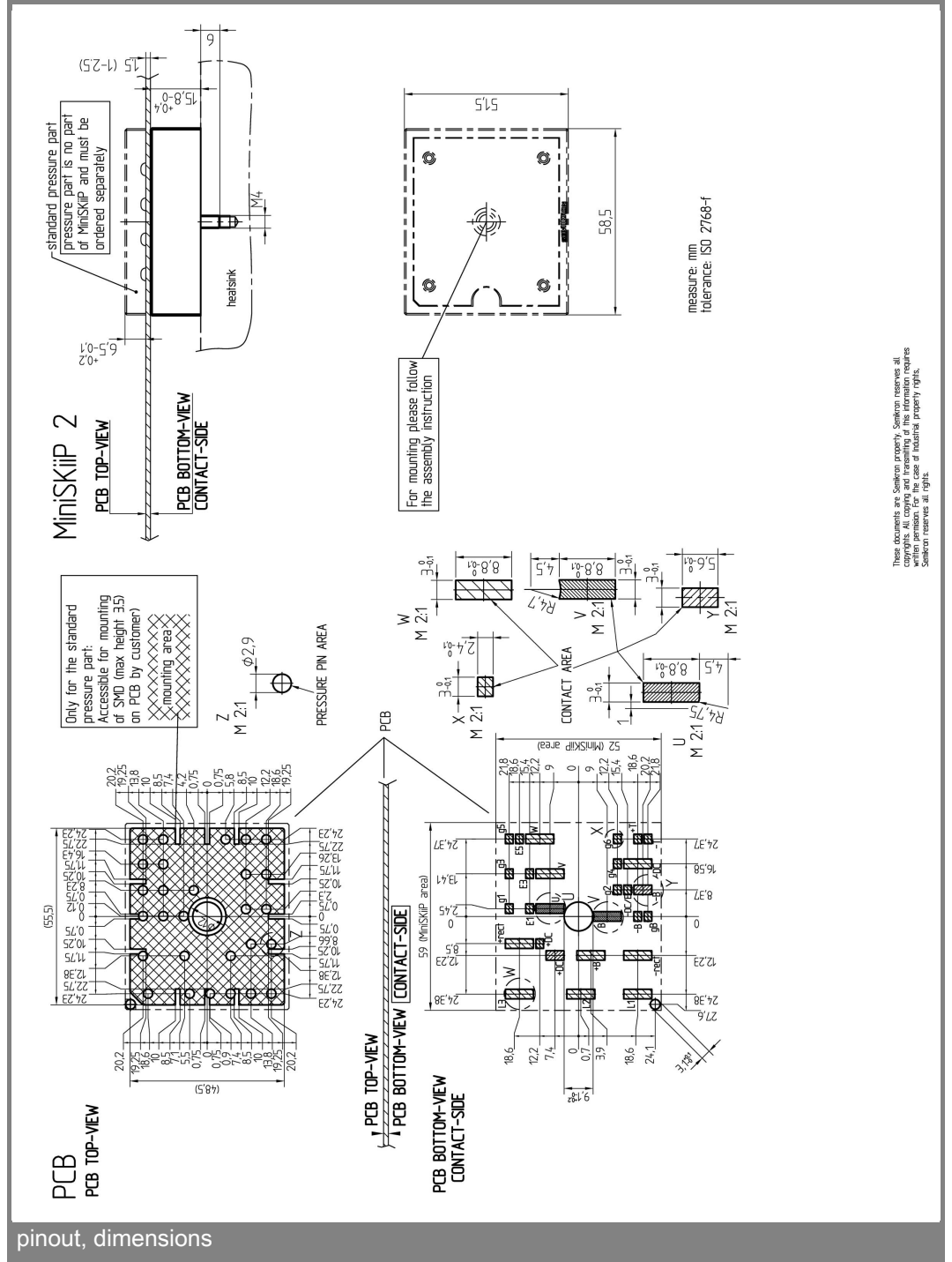
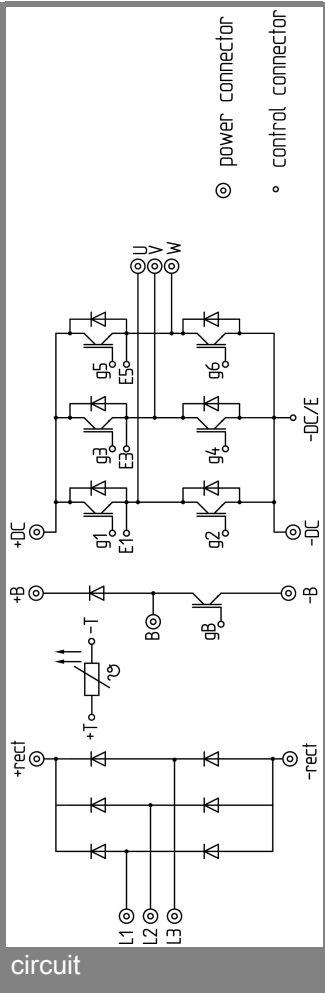


Fig. 10 Typ. input bridge forward characteristic



These documents are Semikron property. Semikron reserves all copyrights. All copying and forwarding of the information requires written permission in case of industrial property rights. Semikron reserves all rights.

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.